



芯基科技

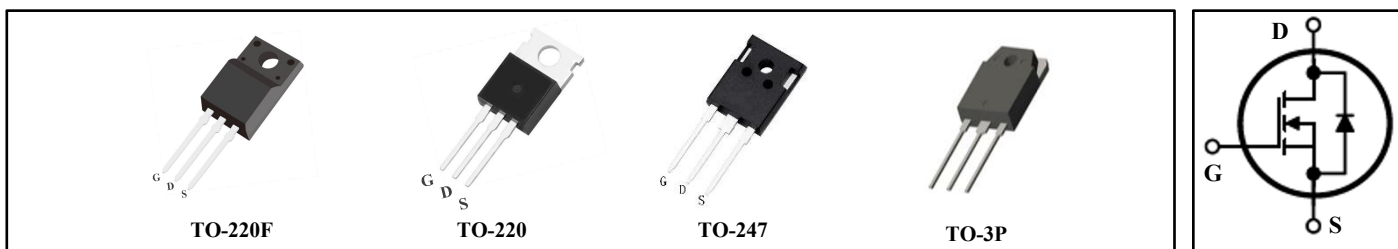
# MPVX20N50B Series Power MOSFET

## FEATURES

- $BV_{DSS}$ : 500V,  $I_D=20A$
- $R_{DS(on)}$  : 0.3Ω(Max) @ $V_{GS}=10V$
- Very Low FOM ( $R_{DS(on)} * Q_g$ )
- Excellent stability and uniformity

## APPLICATIONS

- Switch Mode Power Supply (SMPS)
- Uninterruptible Power Supply (UPS)
- Power Factor Correction (PFC)
- AC to DC Converters



Ordering Information		
Type NO.	Marking	Package Code
MPVA20N50B	MPVA20N50B	TO-220F
MPVP20N50B	MPVP20N50B	TO-220
MPVW20N50B	MPVW20N50B	TO-247
MPVT20N50B	MPVT20N50B	TO-3P

Absolute Maximum Ratings $T_C = 25^\circ C$ , unless otherwise noted				
Parameter	Symbol	Value		Unit
		220F	220-247-3P	
Drain-Source Voltage ( $V_{GS} = 0V$ )	$V_{DSS}$	500		V
Continuous Drain Current	$I_D$	20		A
Pulsed Drain Current (note1)	$I_{DM}$	72		A
Gate-Source Voltage	$V_{GSS}$	$\pm 30$		V
Single Pulse Avalanche Energy (note2)	$E_{AS}$	1000		mJ
Avalanche Current (note1)	$I_{AR}$	12		A
Repetitive Avalanche Energy (note1)	$E_{AR}$	64		mJ
Power Dissipation ( $T_C = 25^\circ C$ )	$P_D$	98	210	W
Operating Junction and Storage Temperature Range	$T_J, T_{stg}$	-55~+150		$^\circ C$

Thermal Resistance				
Parameter	Symbol	Value		Unit
		220F	220-247-3P	
Thermal Resistance, Junction-to-Case	$R_{thJC}$	1.27	0.6	$^\circ C/W$
Thermal Resistance, Junction-to-Ambient	$R_{thJA}$	62.5	60.0	



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# MPVX20N50B Series Power MOSFET

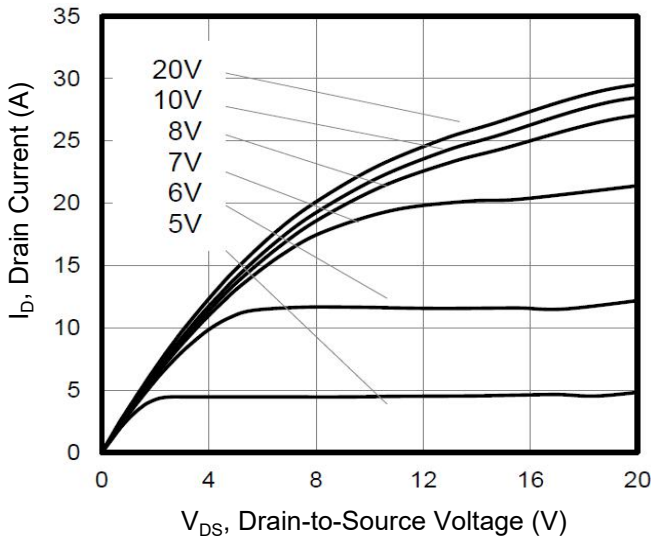
Specifications $T_J = 25^\circ\text{C}$ , unless otherwise noted						
Parameter	Symbol	Test Conditions	Value			Unit
			Min.	Typ.	Max.	
<b>Static</b>						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = 250\mu A$	500	--	--	V
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = 500V, V_{GS} = 0V, T_J = 25^\circ\text{C}$	--	--	1	$\mu A$
Gate-Source Leakage	$I_{GSS}$	$V_{GS} = \pm 30V$	--	--	$\pm 100$	nA
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\mu A$	3.0	--	4.0	V
Drain-Source On-Resistance (Note4)	$R_{DS(on)}$	$V_{GS} = 10V, I_D = 10.0A$	--	0.24	0.30	$\Omega$
<b>Dynamic</b>						
Input Capacitance	$C_{iss}$	$V_{GS} = 0V,$ $V_{DS} = 25V,$ $f = 1.0MHz$	--	3000	--	pF
Output Capacitance	$C_{oss}$		--	221	--	
Reverse Transfer Capacitance	$C_{rss}$		--	16	--	
Total Gate Charge	$Q_g$	$V_{DD} = 400V, I_D = 20.0A,$ $V_{GS} = 10V$	--	75	--	nC
Gate-Source Charge	$Q_{gs}$		--	10	--	
Gate-Drain Charge	$Q_{gd}$		--	31	--	
Turn-on Delay Time	$t_{d(on)}$	$V_{DD} = 250V, I_D = 20.0A,$ $R_G = 25\Omega$	--	35	--	ns
Turn-on Rise Time	$t_r$		--	40	--	
Turn-off Delay Time	$t_{d(off)}$		--	160	--	
Turn-off Fall Time	$t_f$		--	55	--	
<b>Drain-Source Body Diode Characteristics</b>						
Continuous Body Diode Current	$I_S$	$T_C = 25^\circ\text{C}$	--	--	20	A
Pulsed Diode Forward Current	$I_{SM}$		--	--	80	
Body Diode Voltage	$V_{SD}$	$T_J = 25^\circ\text{C}, I_{SD} = 20.0A, V_{GS} = 0V$	--	--	1.4	V
Reverse Recovery Time	$t_{rr}$	$V_{GS} = 0V, I_F = 20.0A,$ $di_F/dt = 100A/\mu s$	--	430	--	ns
Reverse Recovery Charge	$Q_{rr}$		--	6.5	--	$\mu C$

### Notes

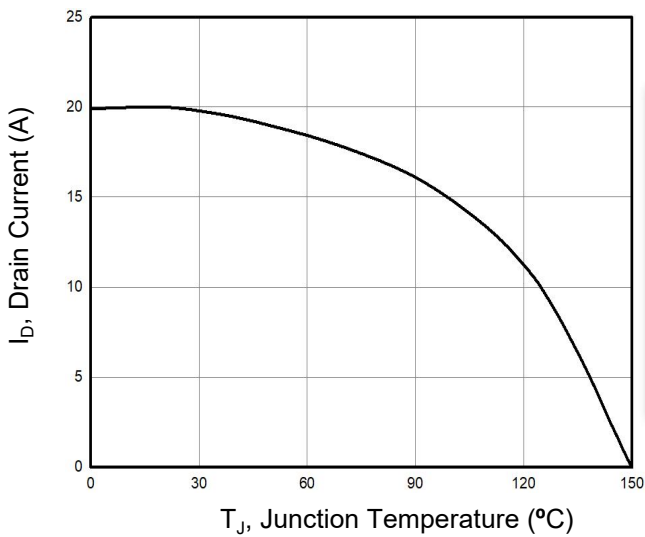
1. Repetitive Rating: Pulse width limited by maximum junction temperature
2.  $I_{AS} = 12A, V_{DD} = 50V, R_G = 25\Omega, \text{Starting } T_J = 25^\circ\text{C}$
3. Pulse Test: Pulse width  $\leq 300\mu s, \text{Duty Cycle } \leq 1\%$
4. Essentially independent of operating temperature

Typical Characteristics  $T_J = 25^\circ\text{C}$ , unless otherwise noted

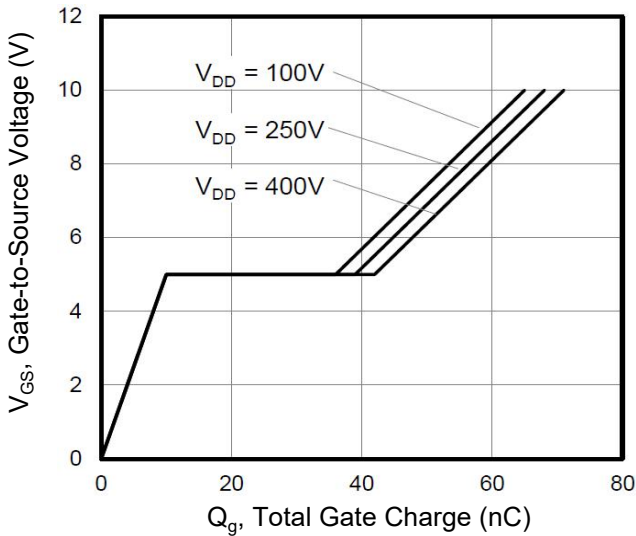
**Figure 1. Output Characteristics**



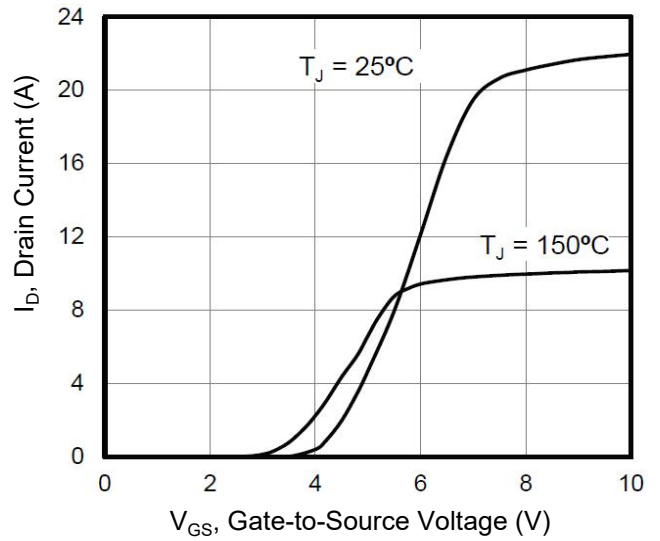
**Figure 3. Drain Current vs. Temperature**



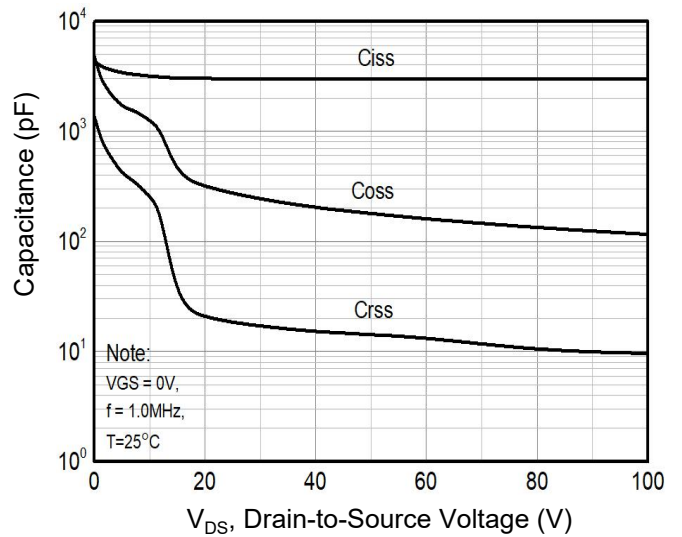
**Figure 5. Gate Charge**



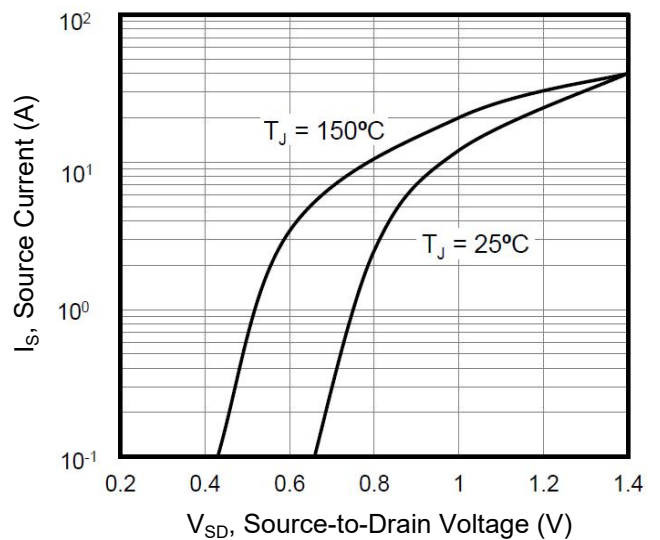
**Figure 2. Transfer Characteristics**



**Figure 4. Capacitance**

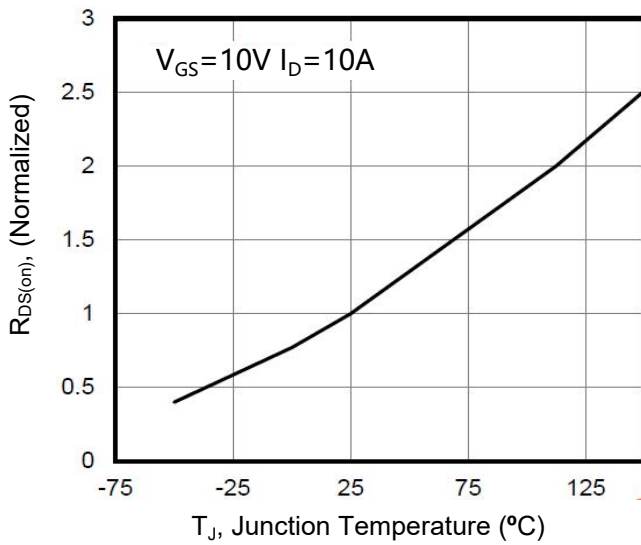


**Figure 6. Body Diode Forward Voltage**

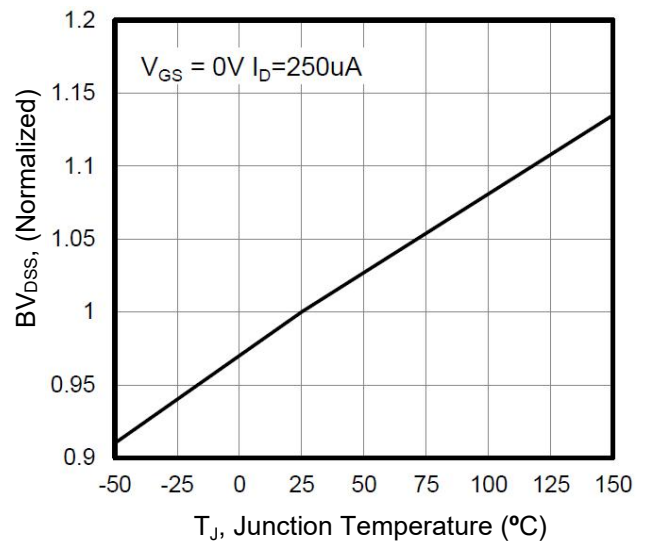


Typical Characteristics  $T_J = 25^\circ\text{C}$ , unless otherwise noted

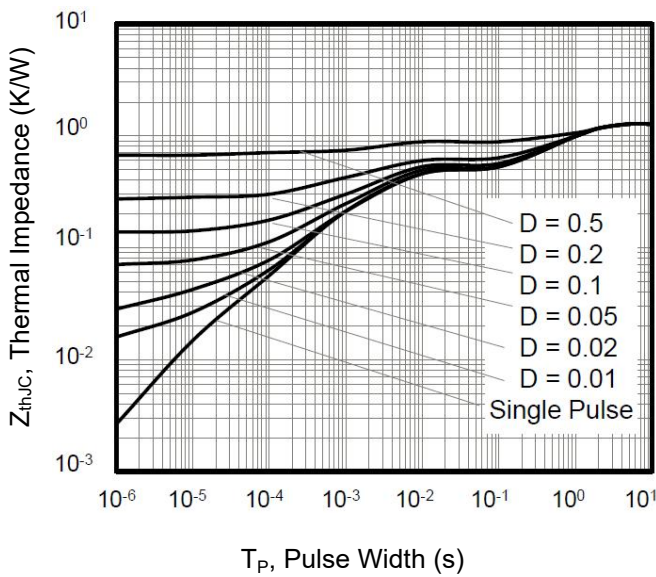
**Figure 7. On-Resistance vs. Temperature**



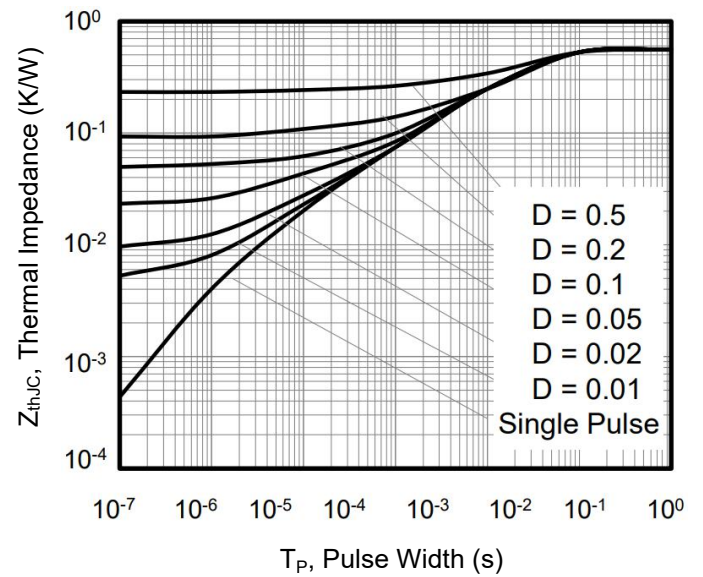
**Figure 8.  $BV_{DSS}$  vs. Temperature**



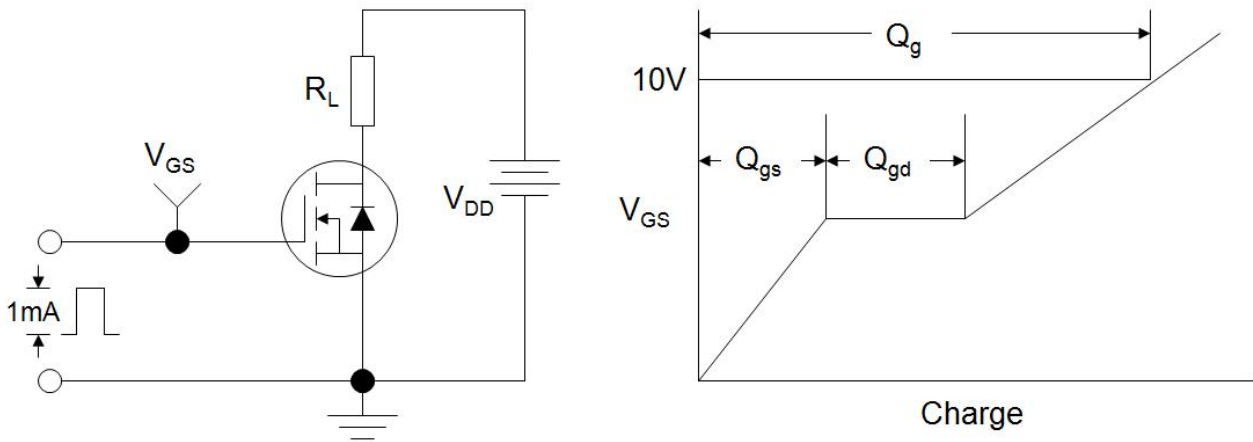
**Figure 9. Transient Thermal Impedance  
(TO-220F)**



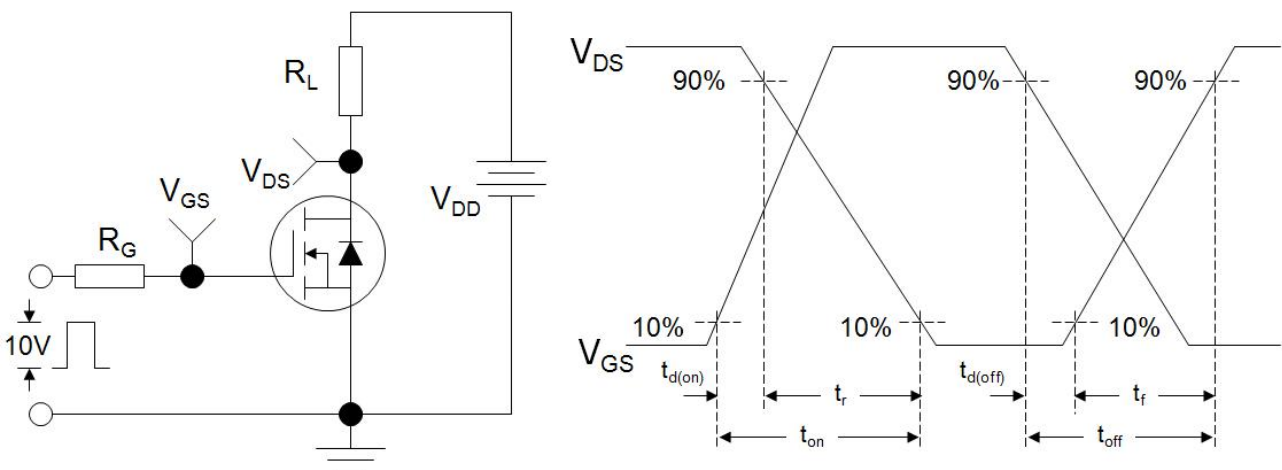
**Figure 10. Transient Thermal Impedance  
(TO-220 TO-247 TO-3P)**



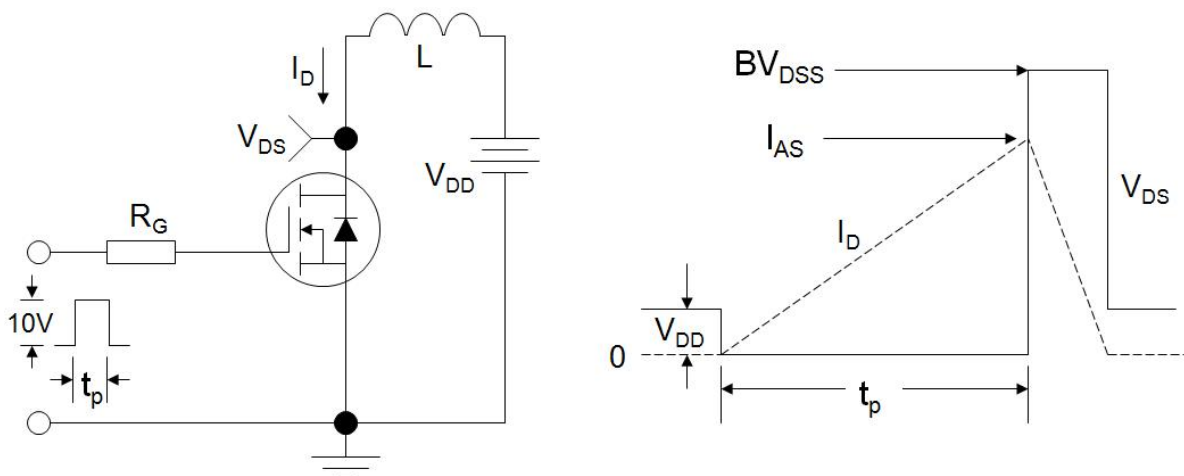
**Figure A: Gate Charge Test Circuit and Waveform**



**Figure B: Resistive Switching Test Circuit and Waveform**



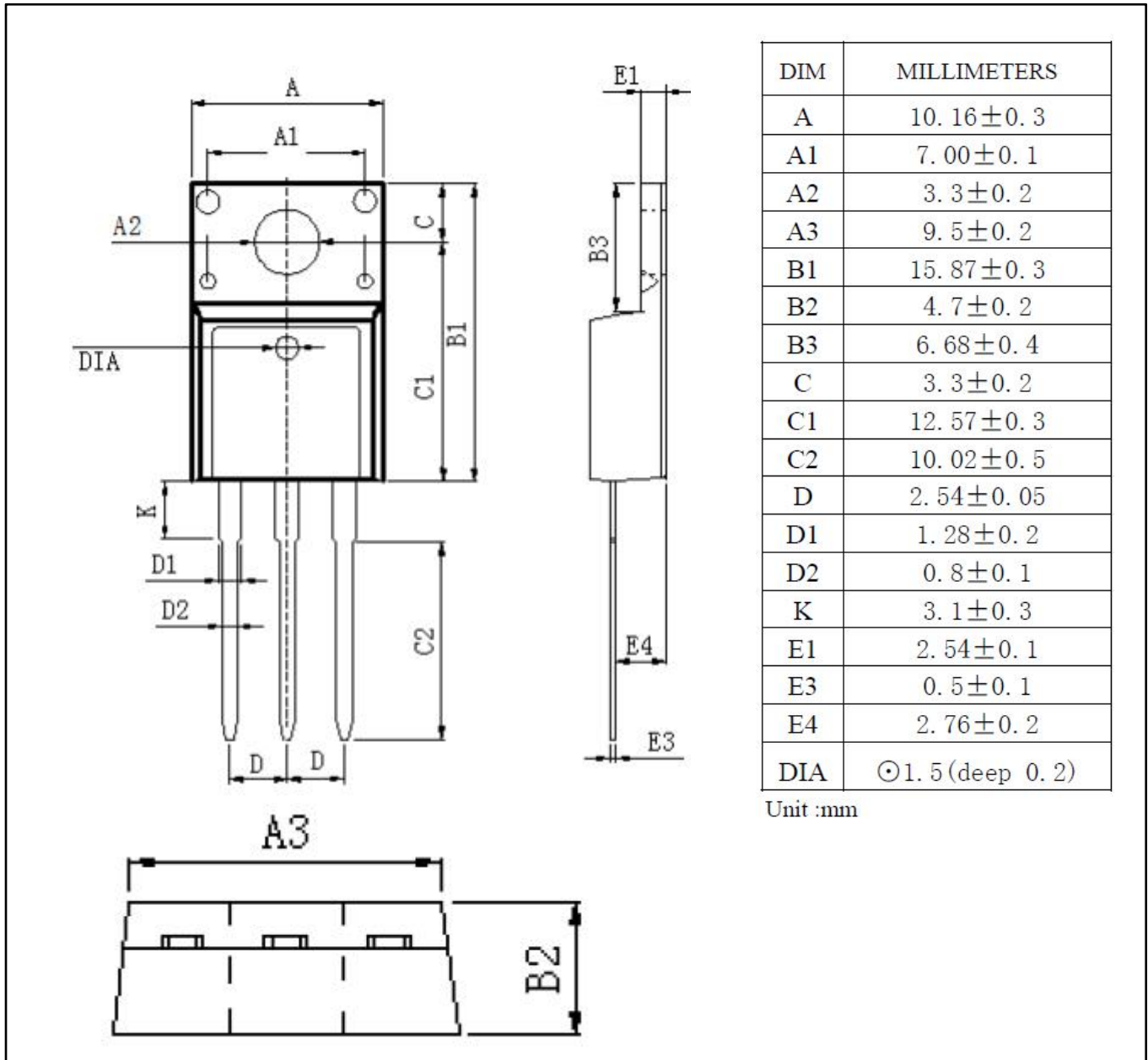
**Figure C: Unclamped Inductive Switching Test Circuit and Waveform**



**Outline Dimension**

Unit: mm

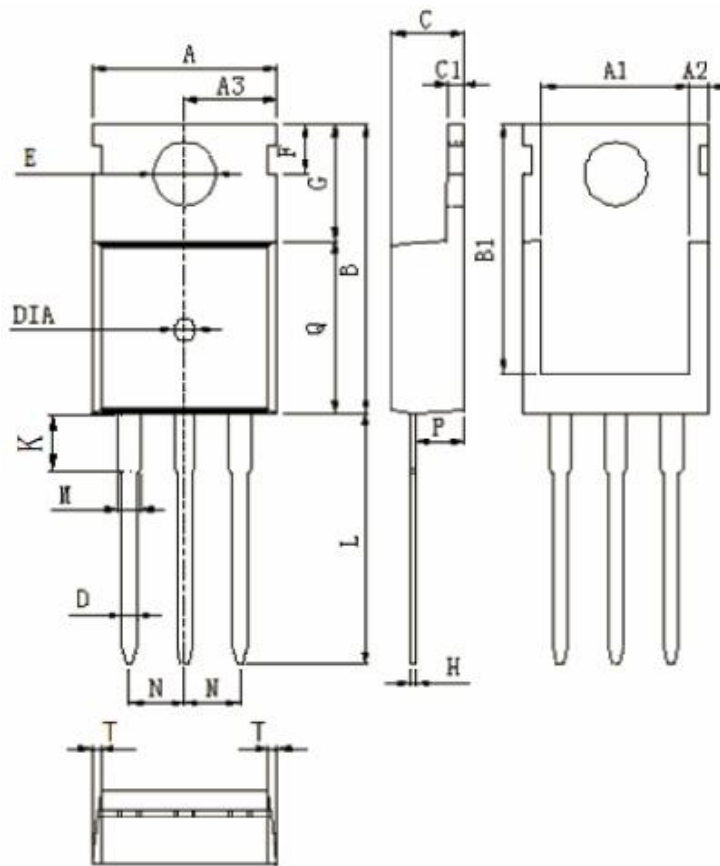
**TO-220F**



Outline Dimension

Unit: mm

TO-220



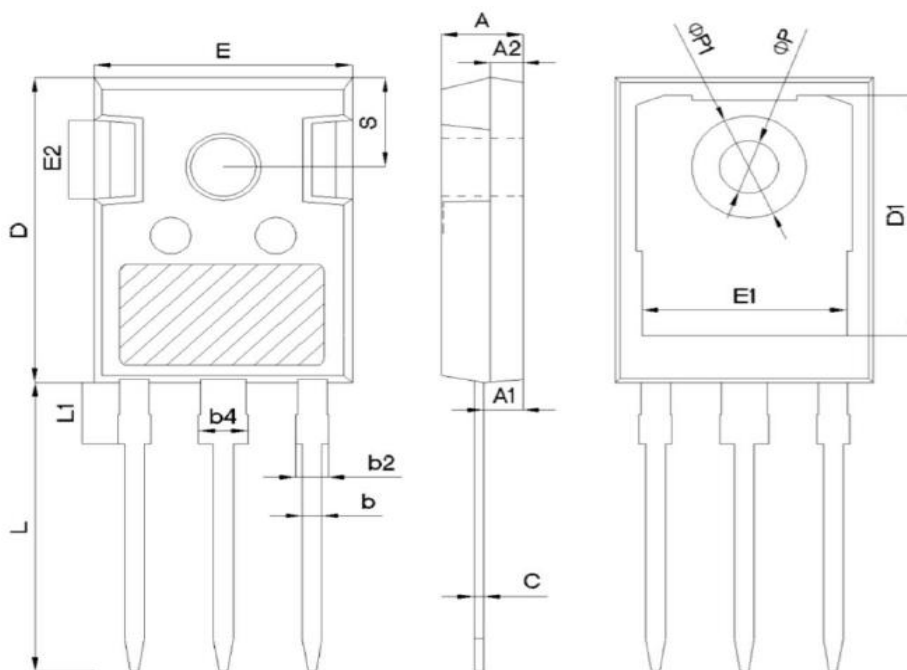
DIM	MILLIMETERS
A	10.0±0.3
A1	8.64±0.2
A2	1.15±0.1
A3	5.0±0.2
B	15.8±0.4
B1	13.2±0.3
C	4.56±0.1
C1	1.3±0.2
D	0.8±0.2
E	3.6±0.2
F	2.95±0.3
G	6.5±0.3
H	0.5±0.1
K	3.1±0.2
L	13.2±0.4
M	1.25±0.1
N	2.54±0.1
P	2.4±0.3
Q	9.0±0.3
T	W:0.35
DIA	⊙1.5(deep 0.2)

Unit :mm

**Outline Dimension**

Unit: mm

**TO-247**



SYMBOL	mm		
	MIN	NOM	MAX
A	4.80	5.00	5.20
A1	2.21	2.41	2.61
A2	1.85	2.00	2.15
b	1.11	1.21	1.36
b2	1.91	2.01	2.21
b4	2.91	3.01	3.21
c	0.51	0.61	0.75
D	20.70	21.00	21.30
D1	16.25	16.55	16.85
E	15.50	15.80	16.10
E1	13.00	13.30	13.60
E2	4.80	5.00	5.20
E3	2.30	2.50	2.70
e	5.44BSC		
L	19.62	19.92	20.22
L1	-	-	4.30
ØP	3.40	3.60	3.80
ØP1	-	-	7.30
S	6.15BSC		



## Outline Dimension

Unit: mm

### TO-3P

